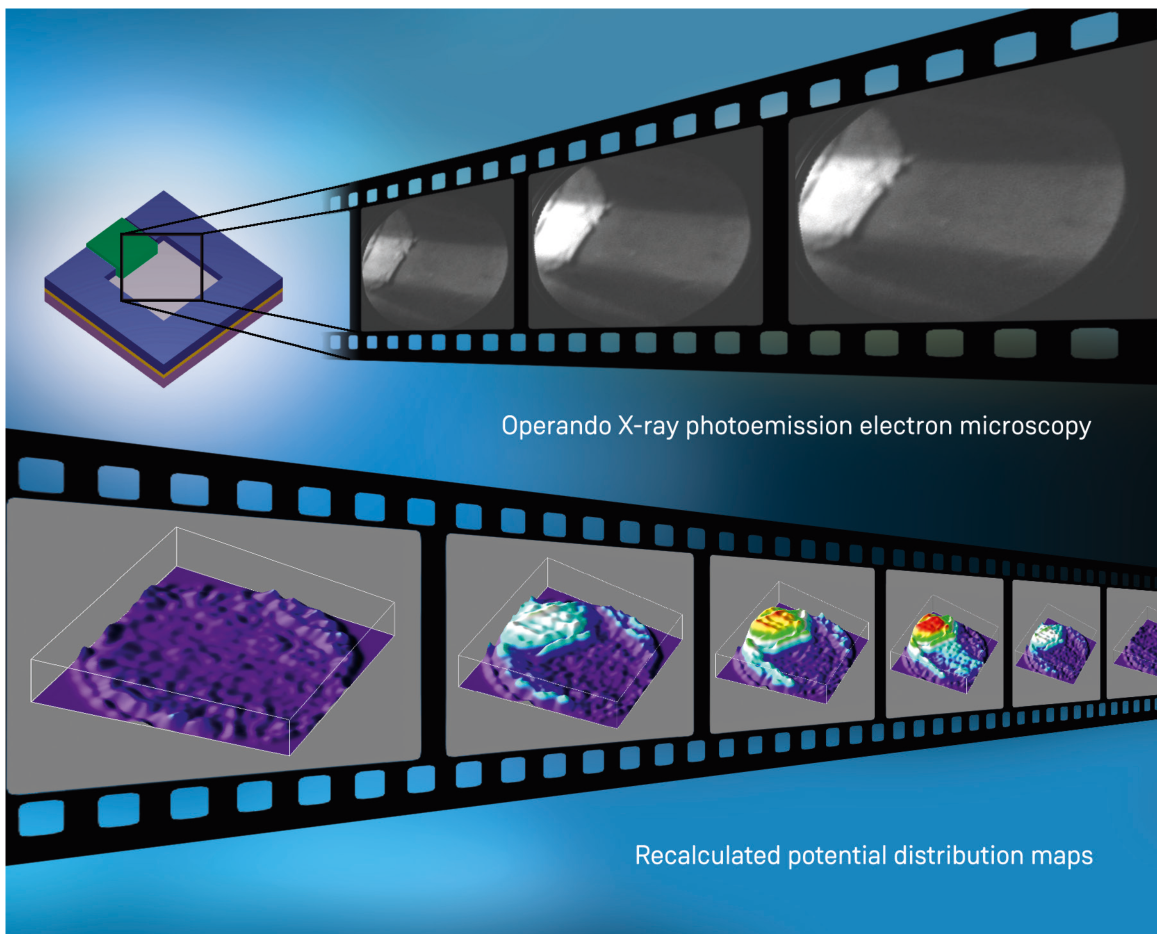

Operando X-ray photoemission electron microscopy (XPEEM) investigations of resistive switching metal-insulator-metal devices

Christoph Jan Schmitz

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Contents

Executive Summary 1

I Part I - Theoretical Background

1 Introduction & Motivation 9

2 Resistive Switching Phenomena 13
2.1 History and state-of-the-art . . . 13
2.1.1 Characteristic I-V dependence in resistive switching materials . . . 14
2.1.2 Geometric location and microscopic shape of conducting channels . . . 14
2.1.3 Resistance modulation and the role of interfaces for filamentary switching . 16
2.1.4 Dynamics of the switching process . . . 17
2.2 Resistive switching oxides . . . 18
2.2.1 Valence change model (VCM) . . . 18
2.2.2 Electronic transport across metal/insulator interfaces . . . 21
2.2.3 Unified compact model for VCM devices . . . 24

3 The model oxide system $SrTiO_3$ 26
3.1 Crystal structure . . . 26
3.2 Electronic properties of $SrTiO_3$ . . . 26
3.3 Structural and electronic correlations: Crystal field splitting in SrTiO3 . . . 28
3.4 Simulations of the Ti L-edge absorption . . . 30

4 Photoelectron emission spectroscopy & microscopy 32
4.1 Three-step model of photoemission . . . 33
4.2 Quantum mechanical description of the excitation process . . . 34
4.2.1 Photoionization cross sections $\sigma_{n,l}$ . . . 35
4.2.2 Dipole selection rules . . . 36
4.3 Probing depth & Surface sensitivity . . . 37
4.4 Electron Spectroscopy for Chemical Analysis (ESCA) . . . 39
4.4.1 X-ray photoemission spectroscopy (XPS) . . . 39
4.4.2 X-ray absorption spectroscopy (XAS) . . . 41
4.5 Photoemission electron microscopy (PEEM) . . . 42
4.6 Photoemission spectromicroscopy using synchrotron light . . . 46

II Part II - Experimental Results

5 Chemical and spatial fingerprints of resistive switching in $SrTiO_3$ 51
5.1 Fingerprints of oxygen vacancies $\mathbf{V}_O^{\cdot\cdot}$ and Ti^{3+} in literature . . . 52
5.2 Chemical fingerprints of reduced STO single crystals . . . 53
5.3 Chemical fingerprints in delaminated STO MIM devices . . . 55
5.3.1 Ti $L_{2,3}$-edge XAS-PEEM . . . 56
5.3.2 O K-edge XAS-PEEM . . . 58
5.3.3 Work function contrast . . . 59
5.3.4 Ti 2p XPS and VB spectroscopy . . . 60
5.4 Spatial fingerprints and filament substructure . . . 61

6 Novel approaches and device concepts for in-situ and operando resistive switching 65
6.1 The top electrode surface sensitivity dilemma . . . 66
6.2 Approach 1: Hard X-ray photoemission electron microscopy (HAXPEEM) . . . 69
6.2.1 Evaluation of HAXPEEM probing depth . . . 70
6.2.2 Interface-Sensitivity and HAXPEEM performance . . . 71
6.2.3 Expected and measured signal intensities . . . 73
6.2.4 Viability of the HAXPEEM approach for time-resolved studies . . . 75
6.3 Approach 2: Planar Devices . . . 78
6.4 Approach 3: Ultra-thin, electron transparent top electrodes . . . 79
6.4.1 XAS attenuation length for Rh electrodes . . . 80
6.4.2 Electron transparency of fabricated, thin-film devices . . . 81
6.5 Summary and Outlook . . . 83

7 In-situ characterization of G/STO thin film devices 86
7.1 Spectromicroscopical quantification of resistive switching filaments . . . 87
7.2 Experiment-assisted device simulations . . . 89
7.3 Absence of chemical fingerprints in in-situ switched devices . . . 91

8 Operando characterization of G/STO thin film devices 92
8.1 Experimental idea . . . 93
8.2 Technical implementation . . . 94
8.2.1 Experimental Setup . . . 94
8.2.2 Sample holder design for operando experiments . . . 94
8.2.3 High voltage surge protection (HVSP) . . . 98
8.2.4 Implementation of temporal resolution in operando XPEEM . . . 99
8.3 Data Analysis: XPEEM based recalculation of local potentials . . . 100
8.3.1 Recalculation of the local potential V(x,y) . . . 100
8.3.2 Recalculation of the local time-dependent potential V(x,y,t) . . . 101
8.3.3 Recalculation of local potentials from intensity modulations . . . 102
8.3.4 Intermixing of chemical and electrostatic information in the recalculation . 105
8.3.5 Limitations of the recalculation algorithm . . . 106
8.4 Experimental results . . . 107
8.4.1 Real-time pulse characterization of G/STO devices in voltage mode . . . 107

8.4.2 Real-time chemical characterization of G/STO devices 117
8.4.3 Hard breakdown (HBD) experiments 122
8.4.4 Scanning electron microscopy (SEM) on post-mortem devices 126
8.5 Summary and discussion of findings 128

9 Summary & Future Perspectives **130**

A Supplementary Information **135**
A.1 Experimental verification of the UHV delamination process 136
A.2 Specifications of instruments and beamlines 137
A.3 Specifications of the HV surge protection implementation 138
A.4 Detailed description of the voltage recalculation procedure in XPEEM 140

Nomenclature **141**

Bibliography **143**

Publications **151**

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